

# EPIGAP Optronik GmbH

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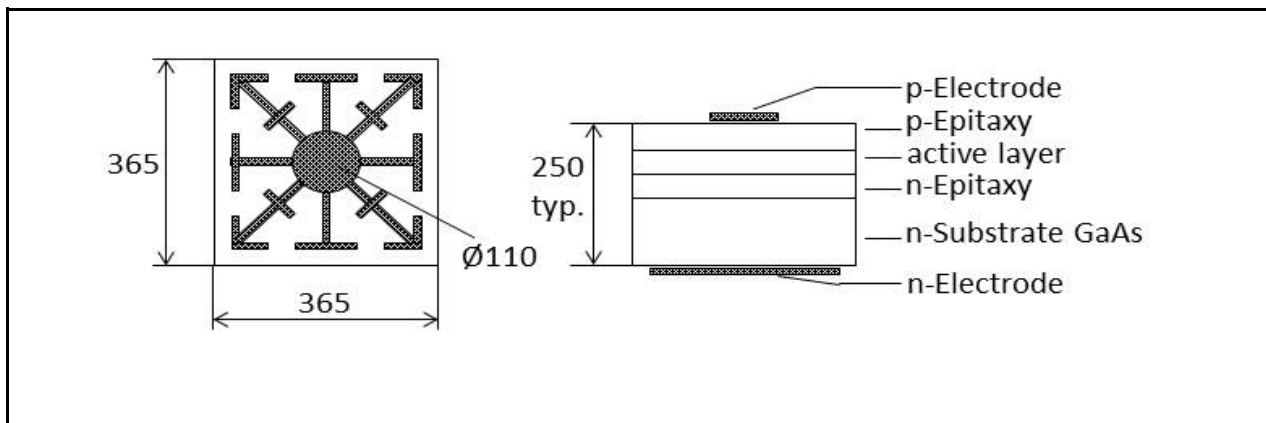
## Data Sheet

### LED Chip Infrared

EOLC-1050-17-1

Rev. 04, 2017

Radiation	Type	Electrodes
Infrared	GaAs, MQW	P (anode) up



### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.15	1.3	V
Forward voltage	$I_F = 100 \text{ mA}$	$V_F$		1.25	1.4	V
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Output power*	$I_F = 50 \text{ mA}$	$\Phi_e$		4.5		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	1030	1050	1070	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		80		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		20		ns

\* Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 114



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.